Pb Free Plating Product

ETU3006S

ThinkiSemi 30Ampere,600Volt Surface Mount Ultrafast Recovery Epitaxial Diode

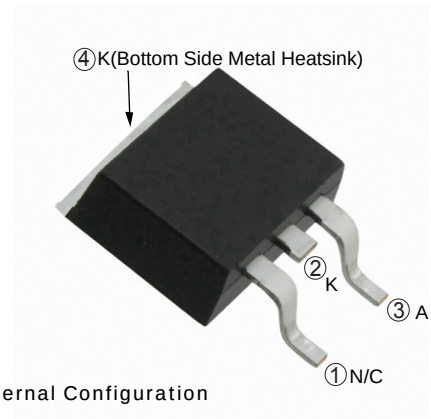
APPLICATION

- Freewheeling, Snubber, Clamp
- Inversion Welder
- PFC
- Plating Power Supply
- Ultrasonic Cleaner and Welder
- Converter & Chopper
- UPS

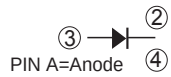
PRODUCT FEATURE

- Ultrafast Recovery Time
- Soft Recovery Characteristics
- Low Recovery Loss
- Low Forward Voltage
- High Surge Current Capability
- Low Leakage Current

TO-263/D2PAK(SMD-220)-SQ



Internal Configuration



② PIN K=Cathode

④ CASE K=Cathode

① PIN N/C(None Collect)

GENERAL DESCRIPTION

ETU3006S using THINKISEMI lastest FRED FAB process(planar passivation pellet) with ultrafast and soft recovery characteristics.

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Peak repetitive reverse voltage	V_{RRM}		600	V
Average rectified forward current in DC	$I_{F(AV)}$	T_C = 130 °C	30	A
Non-repetitive peak surge current	I_{FSM}	T_J = 25 °C	200	
Operating junction and storage temperatures	T_J, T_{Stg}		-65 to +175	°C

ELECTRICAL SPECIFICATIONS (T_J = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Breakdown voltage, blocking voltage	V_{BR}, V_R	I_R = 100 µA	600	-	-	V
Forward voltage	V_F	I_F = 30 A	-	1.4	2.0	
		I_F = 30 A, T_J = 150 °C	-	1.15	1.35	
Reverse leakage current	I_R	V_R = V_R rated	-	0.02	30	µA
		T_J = 150 °C, V_R = V_R rated	-	30	250	
Junction capacitance	C_T	V_R = 600 V	-	20	-	pF
Series inductance	L_S	Measured lead to lead 5 mm from package body	-	8	-	nH

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DYNAMIC RECOVERY CHARACTERISTICS (T_J = 25 °C unless otherwise specified)							
PARAMETER	**SYMBOL**	**TEST CONDITIONS**		**MIN.**	**TYP.**	**MAX.**	**UNITS**
Reverse recovery time	t_{rr}	I_F = 1 A, dI_F/dt = 50 A/µs, V_R = 30 V		-	30	45	ns
		T_J = 25 °C	I_F = 30 A, dI_F/dt = 200 A/µs, V_R = 200 V	-	45	-	
		T_J = 125 °C		-	100	-	
Peak recovery current	I_{RRM}	T_J = 25 °C		-	5.6	-	A
		T_J = 125 °C		-	10	-	
Reverse recovery charge	Q_{rr}	T_J = 25 °C		-	127	-	nC
		T_J = 125 °C		-	580	-	

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	**SYMBOL**	**TEST CONDITIONS**	**MIN.**	**TYP.**	**MAX.**	**UNITS**
Maximum junction and storage temperature range	T_J, T_{Stg}		-65	-	175	°C
Thermal resistance, junction-to-case	R_{thJC}		-	0.84	1.3	°C/W
Thermal resistance, junction-to-ambient	R_{thJA}	Typical socket mount	-	-	70	
Typical thermal resistance, case-to-heatsink	R_{thCS}	Mounting surface, flat, smooth, and greased	-	0.5	-	
Weight			-	2	-	g
			-	0.07	-	oz.
Mounting torque			6 (5)	-	12 (10)	kgf · cm (lbf · in)
Marking device		Case style TO-263/D2PAK(SMD-220)-SQ	ETU3006S			

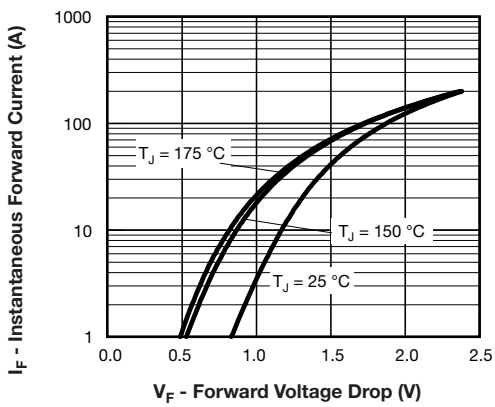

Fig. 1 - Typical Forward Voltage Drop Characteristics

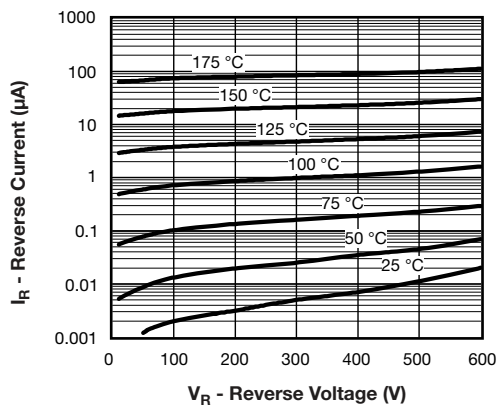

Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

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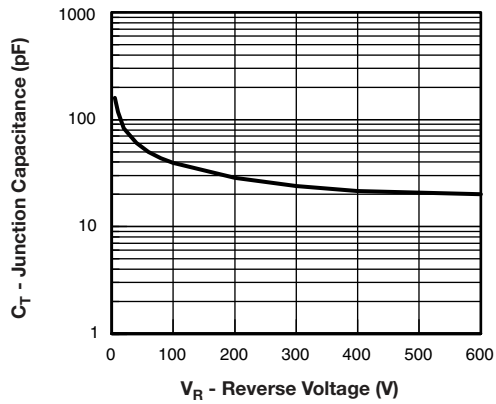

Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

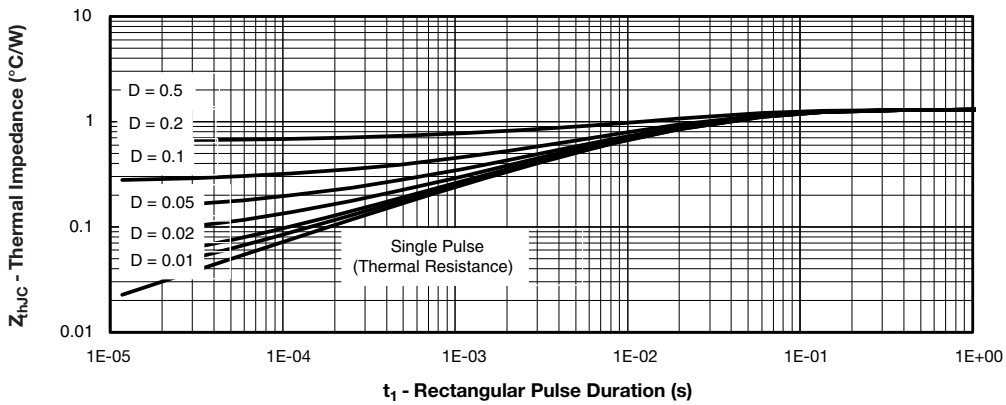

Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

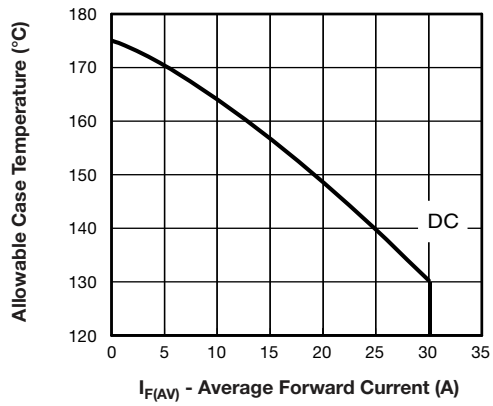

Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

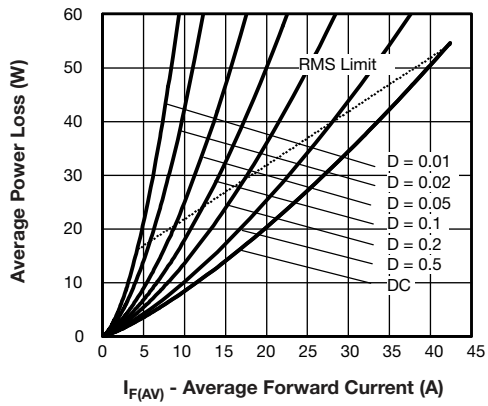

Fig. 6 - Forward Power Loss Characteristics

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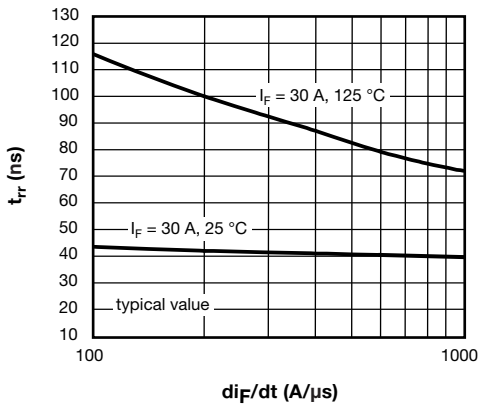


Fig. 7 - Typical Reverse Recovery vs. dI_F/dt

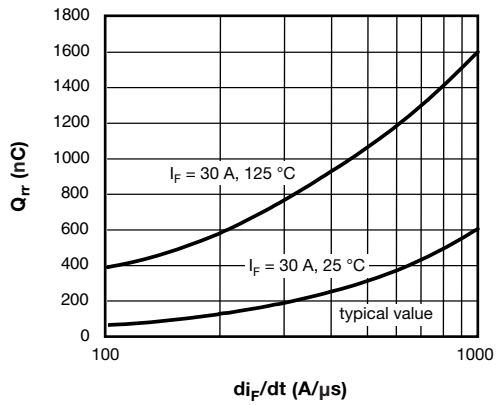
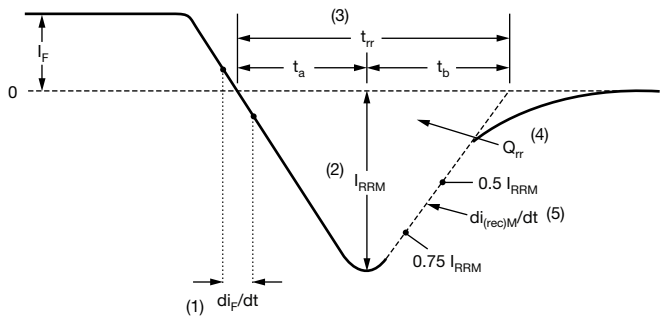


Fig. 8 - Typical Stored Charge vs. dI_F/dt



(1) di_F/dt - rate of change of current through zero crossing

(2) I_{RRM} - peak reverse recovery current

(3) t_{rr} - reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.

(4) Q_{rr} - area under curve defined by t_{rr} and I_{RRM}

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) $di_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

Fig. 9 - Reverse Recovery Waveform and Definitions

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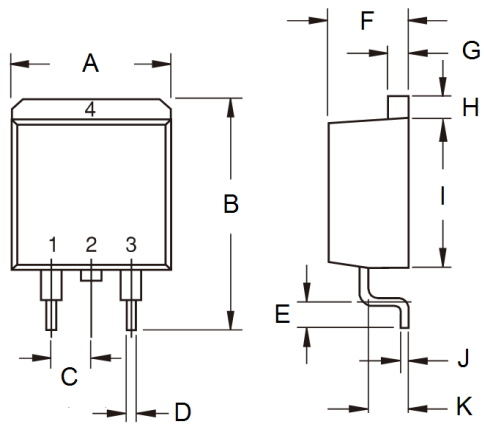
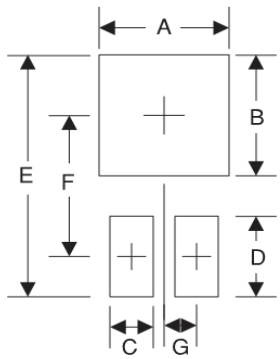
Mechancal Dimensions THINKI TO-263/D2PAK(SMD-220)-SQ



DIM.	Unit (mm)		Unit (inch)	
	Min	Max	Min	Max
A	-	10.5	-	0.413
B	14.60	15.88	0.575	0.625
C	2.41	2.67	0.095	0.105
D	0.68	0.94	0.027	0.037
E	2.29	2.79	0.090	0.110
F	4.44	4.70	0.175	0.185
G	1.14	1.40	0.045	0.055
H	1.14	1.40	0.045	0.055
I	8.25	9.25	0.325	0.364
J	0.36	0.53	0.014	0.021
K	2.03	2.79	0.080	0.110

SUGGESTED PAD LAYOUT



Symbol	Unit (mm)	Unit (inch)
A	10.8	0.425
B	8.3	0.327
C	1.1	0.043
D	3.5	0.138
E	16.9	0.665
F	9.5	0.374
G	2.5	0.098

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